

9A High-Speed MOSFET Drivers

Features

- High Peak Output Current: 10A (typ.)
- Low Shoot-Through/Cross-Conduction Current in Output Stage
- Wide Input Supply Voltage Operating Range:
 - 4.5V to 18V
- High Continuous Output Current: 2A (max.)
- Matched Fast Rise and Fall Times:
 - 15 ns with 4,700 pF Load
 - 135 ns with 47,000 pF Load
- Matched Short Propagation Delays: 42 ns (typ.)
- Low Supply Current:
 - With Logic '1' Input 130 μA (typ.)
 - With Logic '0' Input 33 μA (typ.)
- Low Output Impedance: 1.2Ω (typ.)
- Latch-Up Protected: Will Withstand 1.5A Output Reverse Current
- Input Will Withstand Negative Inputs Up To 5V
- Pin-Compatible with the TC4420/TC4429 and TC4421/TC4422 MOSFET Drivers
- Space-Saving, Thermally-Enhanced, 8-Pin DFN Package

Applications

- Line Drivers for Extra Heavily-Loaded Lines
- Pulse Generators
- · Driving the Largest MOSFETs and IGBTs
- Local Power ON/OFF Switch
- · Motor and Solenoid Driver
- LF Initiator

General Description

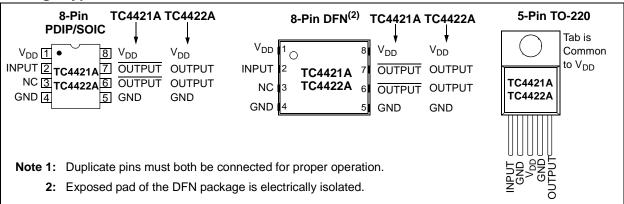
The TC4421A/TC4422A are improved versions of the earlier TC4421/TC4422 family of single-output MOSFET drivers. These devices are high-current buffer/drivers capable of driving large MOSFETs and Insulated Gate Bipolar Transistors (IGBTs). The TC4421A/TC4422A have matched output rise and fall times, as well as matched leading and falling-edge propagation delay times. The TC4421A/TC4422A devices also have very low cross-conduction current, reducing the overall power dissipation of the device.

These devices are essentially immune to any form of upset, except direct overvoltage or over-dissipation. They cannot be latched under any conditions within their power and voltage ratings. These parts are not subject to damage or improper operation when up to 5V of ground bounce is present on their ground terminals. They can accept, without damage or logic upset, more than 1A inductive current of either polarity being forced back into their outputs. In addition, all terminals are fully protected against up to 4 kV of electrostatic discharge.

The TC4421A/TC4422A inputs may be driven directly from either TTL or CMOS (3V to 18V). In addition, 300 mV of hysteresis is built into the input, providing noise immunity and allowing the device to be driven from slowly rising or falling waveforms.

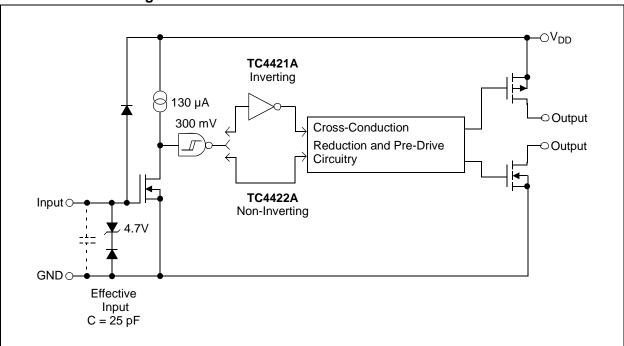
With both surface-mount and pin-through-hole packages, in addition to a wide operating temperature range, the TC4421A/TC4422A family of 9A MOSFET drivers fit into most any application where high gate/line capacitance drive is required.

Package Types⁽¹⁾



www.DataSheet4U.com

Functional Block Diagram



www.DataSheet4LL.com

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

Supply Voltage	+20V
Input Voltage(V _{DD}	+ 0.3V) to (GND - 5V)
Input Current (V _{IN} > V _{DD})	50 mA

† Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.										
Parameters	Sym	Min	Тур	Max	Units	Conditions				
Input	Input									
Logic '1', High Input Voltage	V _{IH}	2.4	1.8	_	V					
Logic '0', Low Input Voltage	V _{IL}	_	1.3	0.8	V					
Input Current	I _{IN}	-10	1	+10	μΑ	$0V \le V_{IN} \le V_{DD}$				
Input Voltage	V _{IN}	-5	_	V _{DD} – 0.3	V					
Output										
High Output Voltage	V _{OH}	$V_{DD} - 0.025$	l		V	DC Test				
Low Output Voltage	V _{OL}	_		0.025	V	DC Test				
Output Resistance, High	R _{OH}	_	1.25	1.5	Ω	I _{OUT} = 10 mA, V _{DD} = 18V				
Output Resistance, Low	R _{OL}	_	0.8	1.1	Ω	I _{OUT} = 10 mA, V _{DD} = 18V				
Peak Output Current	I _{PK}	_	10.0	_	Α	V _{DD} = 18V				
Continuous Output Current	I _{DC}	2	_	_	A	$10V \le V_{DD} \le 18V$, $T_A = +25^{\circ}C$ (TC4421A/TC4422A CAT only) (Note 2)				
Latch-Up Protection Withstand Reverse Current	I _{REV}	_	>1.5	_	Α	Duty cycle ≤ 2%, t ≤ 300 µsec				
Switching Time (Note 1)										
Rise Time	t _R	_	28	34	ns	Figure 4-1 , C _L = 10,000 pF				
Fall Time	t _F	_	26	32	ns	Figure 4-1 , C _L = 10,000 pF				
Propagation Delay Time	t _{D1}	_	38	45	ns	Figure 4-1 , C _L = 10,000 pF				
Propagation Delay Time	t _{D2}	_	42	49	ns	Figure 4-1 , C _L = 10,000 pF				
Power Supply										
Power Supply Current	I _S	_	130	250	μΑ	V _{IN} = 3V				
		_	35	100	μΑ	V _{IN} = 0V				
Operating Input Voltage	V_{DD}	4.5	_	18	V					

Note 1: Switching times ensured by design.

2: Tested during characterization, not production tested.

www.DataSheeta

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise noted, over operating temperature range with $4.5V \le V_{DD} \le 18V$.								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
Input								
Logic '1', High Input Voltage	V_{IH}	2.4	l	_	V			
Logic '0', Low Input Voltage	V_{IL}	_		0.8	V			
Input Current	I _{IN}	-10	_	+10	μA	$0V \le V_{IN} \le V_{DD}$		
Output								
High Output Voltage	V _{OH}	V _{DD} - 0.025	_	_	V	DC Test		
Low Output Voltage	V _{OL}	_	_	0.025	V	DC Test		
Output Resistance, High	R _{OH}	_	_	2.0	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Output Resistance, Low	R _{OL}	_	_	1.6	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Switching Time (Note 1)								
Rise Time	t _R	_	38	45	ns	Figure 4-1 , C _L = 10,000 pF		
Fall Time	t _F	_	33	40	ns	Figure 4-1 , C _L = 10,000 pF		
Propagation Delay Time	t _{D1}	_	50.4	60	ns	Figure 4-1 , C _L = 10,000 pF		
Propagation Delay Time	t _{D2}	_	53	60	ns	Figure 4-1 , C _L = 10,000 pF		
Power Supply								
Power Supply Current	I _S	_	200	500	μA	V _{IN} = 3V		
		_	50	150	μA	V _{IN} = 0V		
Operating Input Voltage	V_{DD}	4.5		18	V			

Note 1: Switching times ensured by design.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with 4.5V ≤ V _{DD} ≤ 18V.								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
Temperature Ranges								
Specified Temperature Range (V)	T _A	-40	_	+125	°C			
Maximum Junction Temperature	TJ	_	_	+150	°C			
Storage Temperature Range	T _A	-65	_	+150	°C			
Package Thermal Resistances								
Thermal Resistance, 5L-TO-220	θ_{JA}	_	71	_	°C/W	Without heat sink		
Thermal Resistance, 8L-6x5 DFN	θ_{JA}	_	33.2	_	°C/W	Typical 4-layer board with vias to ground plane		
Thermal Resistance, 8L-PDIP	θ_{JA}	_	125	_	°C/W			
Thermal Resistance, 8L-SOIC	θ_{JA}	_	155	_	°C/W			

www.DataSheet4II.com

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with 4.5V $\leq V_{DD} \leq 18V$.

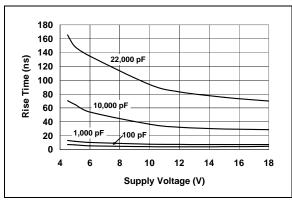


FIGURE 2-1: Rise Time vs. Supply Voltage.

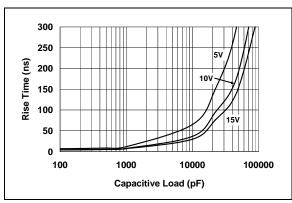


FIGURE 2-2: Rise Time vs. Capacitive Load.

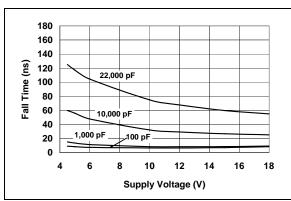


FIGURE 2-3: Fall Time vs. Supply Voltage.

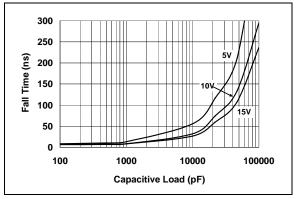


FIGURE 2-4: Fall Time vs. Capacitive Load.

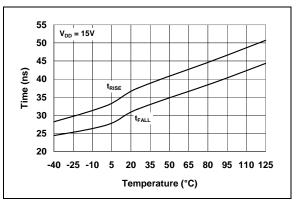


FIGURE 2-5: Rise and Fall Times vs. Temperature.

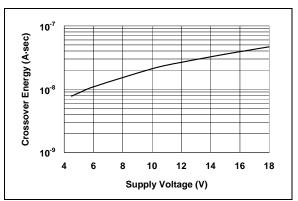


FIGURE 2-6: Crossover Energy vs Supply Voltage.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

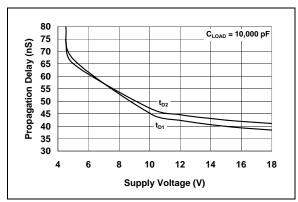


FIGURE 2-7: Propagation Delay vs. Supply Voltage.

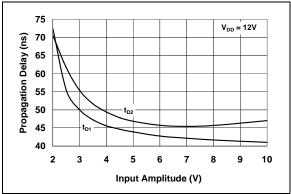


FIGURE 2-8: Propagation Delay vs. Input Amplitude.

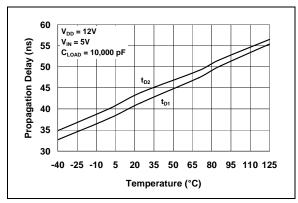


FIGURE 2-9: Propagation Delay vs. Temperature.

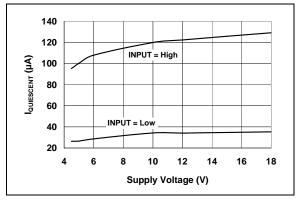


FIGURE 2-10: Quiescent Supply Current vs. Supply Voltage.

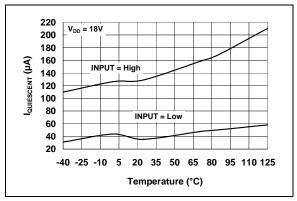


FIGURE 2-11: Quiescent Supply Current vs. Temperature.

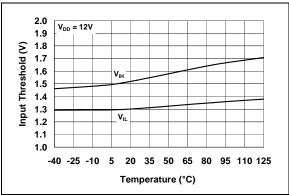


FIGURE 2-12: Input Threshold vs. Temperature.

ww.DataSheet4U.com

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

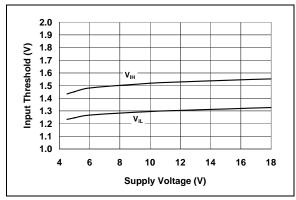


FIGURE 2-13: Input Threshold vs. Supply Voltage.

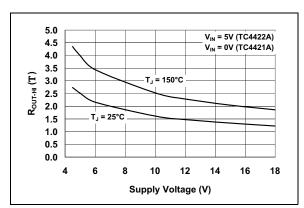


FIGURE 2-14: High-State Output Resistance vs. Supply Voltage.

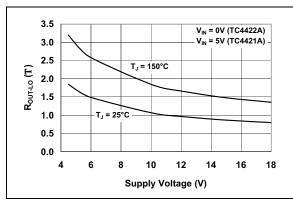


FIGURE 2-15: Low-State Output Resistance vs. Supply Voltage.

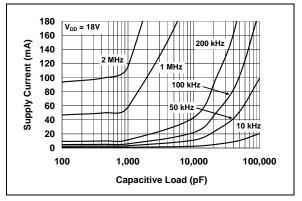


FIGURE 2-16: Supply Current vs. Capactive Load ($V_{DD} = 18V$).

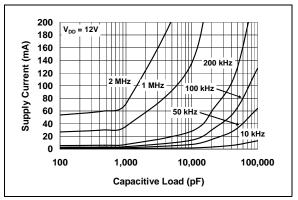


FIGURE 2-17: Supply Current vs. Capactive Load ($V_{DD} = 12V$).

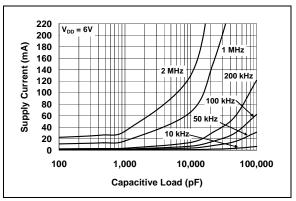


FIGURE 2-18: Supply Current vs. Capactive Load $(V_{DD} = 6V)$.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with 4.5V $\leq V_{DD} \leq 18V$.

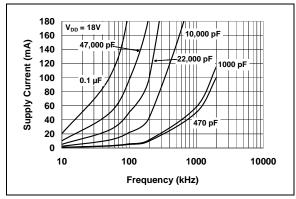


FIGURE 2-19: Supply Current vs. Frequency $(V_{DD} = 18V)$.

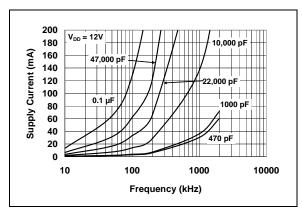


FIGURE 2-20: Supply Current vs. Frequency $(V_{DD} = 12V)$.

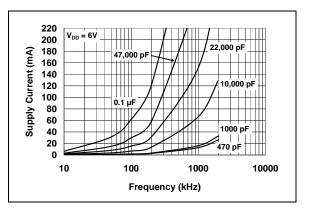


FIGURE 2-21: Supply Current vs. Frequency $(V_{DD} = 6V)$.

www.DataSheet4II.com

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No. 8-Pin PDIP, SOIC	Pin No. 8-Pin DFN	Pin No. 5-Pin TO-220	Symbol	Description
1	1	_	V_{DD}	Supply input, 4.5V to 18V
2	2	1	INPUT	Control input, TTL/CMOS-compatible input
3	3	_	NC	No connection
4	4	2	GND	Ground
5	5	4	GND	Ground
6	6	5	OUTPUT	CMOS push-pull output
7	7	_	OUTPUT	CMOS push-pull output
8	8	3	V_{DD}	Supply input, 4.5V to 18V
_	PAD	_	NC	Exposed metal pad
_	_	TAB	V_{DD}	Metal tab is at the V _{DD} potential

3.1 Supply Input (V_{DD})

The V_{DD} input is the bias supply for the MOSFET driver and is rated for 4.5V to 18V with respect to the ground pin. The V_{DD} input should be bypassed to ground with a local ceramic capacitor. The value of the capacitor should be chosen based on the capacitive load that is being driven. A minimum value of 1.0 μ F is suggested.

3.2 Control Input

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input also has 300 mV of hysteresis between the high and low thresholds that prevents output glitching even when the rise and fall time of the input signal is very slow.

3.3 CMOS Push-Pull Output

The MOSFET driver output is a low-impedance, CMOS, push-pull style output capable of driving a capacitive load with 9.0A peak currents. The MOSFET driver output is capable of withstanding 1.5A peak reverse currents of either polarity.

3.4 Ground

The ground pins are the return path for the bias current and for the high peak currents that discharge the load capacitor. The ground pins should be tied into a ground plane or have very short traces to the bias supply source return.

3.5 Exposed Metal Pad

The exposed metal pad of the 6x5 DFN package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a Printed Circuit Board (PCB) to aid in heat removal from the package.

3.6 Metal Tab

The metal tab of the TO-220 package is connected to the V_{DD} potential of the device. This connection to V_{DD} can be used as a current carrying path for the device.

www.DataSheet4U.com

4.0 APPLICATIONS INFORMATION

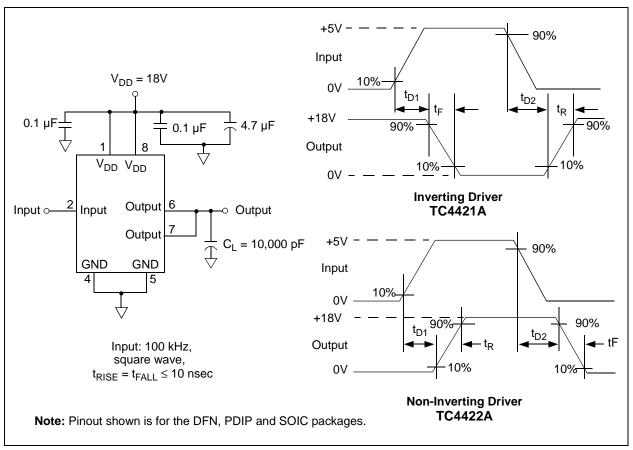


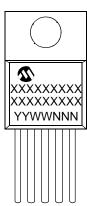
FIGURE 4-1: Switching Time Test Circuits.

www.DataSheet4LL.com

5.0 PACKAGING INFORMATION

5.1 Package Marking Information

5-Lead TO-220



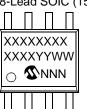
8-Lead DFN



8-Lead PDIP (300 mil)



8-Lead SOIC (150 mil)



Example:



Example:



Example:



Example:



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

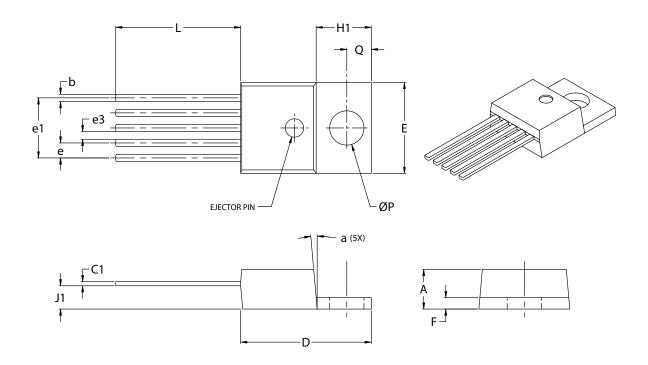
NNN Alphanumeric traceability code

(e3) Pb-free JEDEC designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

5-Lead Plastic Transistor Outline (AT) (TO-220)



	Units		ES*	MILLIMETERS		
Dimension Limi	Dimension Limits		MAX	MIN	MAX	
Lead Pitch	е	.060	.072	1.52	1.83	
Overall Lead Centers	e1	.263	.273	6.68	6.93	
Space Between Leads	e3	.030	.040	0.76	1.02	
Overall Height	Α	.160	.190	4.06	4.83	
Overall Width	E	.385	.415	9.78	10.54	
Overall Length	D	.560	.590	14.22	14.99	
Flag Length	H1	.234	.258	5.94	6.55	
Flag Thickness	F	.045	.055	1.14	1.40	
Through Hole Center	Q	.103	.113	2.62	2.87	
Through Hole Diameter	Р	.146	.156	3.71	3.96	
Lead Length	L	.540	.560	13.72	14.22	
Base to Bottom of Lead	J1	.090	.115	2.29	2.92	
Lead Thickness	C1	.014	.022	0.36	0.56	
Lead Width	b	.025	.040	0.64	1.02	
Mold Draft Angle	a	3°	7°	3°	7°	

^{*}Controlling Parameter

Notes:

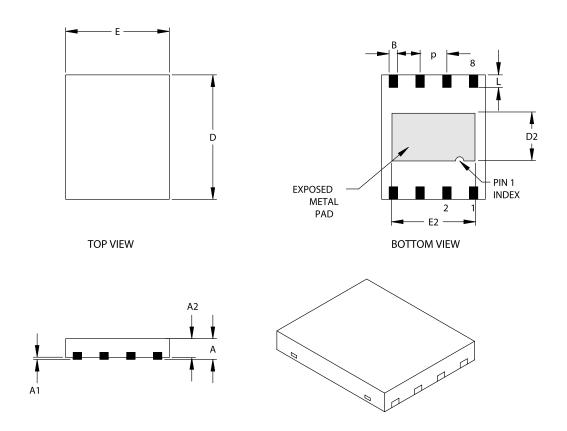
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC equivalent: TO-220

Drawing No. C04-036

www.DataSheet4LL.com

8-Lead Plastic Dual Flat No Lead Package (MF) 6x5 mm Body (DFN-S) - Saw Singulated



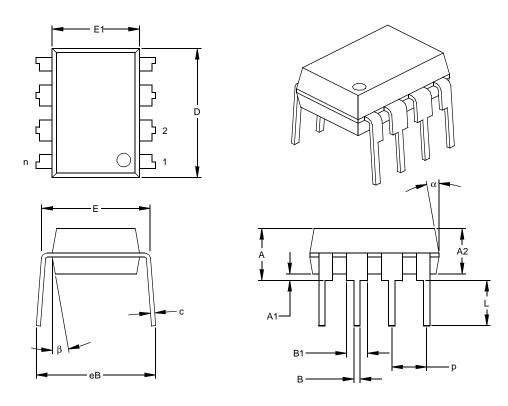
	Units		INCHES		М	ILLIMETERS*	
Dimension	Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.050 BSC			1.27 BSC	
Overall Height	А	.033	.035	.037	0.85	0.90	0.95
Package Thickness	A2	.031	.035	.037	0.80	0.89	0.95
Standoff	A1	.000	.0004	.002	0.00	0.01	0.05
Base Thickness	A3	.007	.008	.009	0.17	0.20	0.23
Overall Length	E	.195	.197	.199	4.95	5.00	5.05
Exposed Pad Length	E2	.152	.157	.163	3.85	4.00	4.15
Overall Width	D	.234	.236	.238	5.95	6.00	6.05
Exposed Pad Width	D2	.089	.091	.093	2.25	2.30	2.35
Lead Width	В	.014	.016	.019	0.35	0.40	0.47
Lead Length	L	.024		.026	0.60		0.65

Notes:

JEDEC equivalent: MO-220

Drawing No. C04-122 Revised 11/3/03

8-Lead Plastic Dual In-line (PA) - 300 mil (PDIP)



	Units	INCHES*			N	IILLIMETERS	3
Dimensi	on Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.100			2.54	
Top to Seating Plane	Α	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	Е	.300	.313	.325	7.62	7.94	8.26
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60
Overall Length	D	.360	.373	.385	9.14	9.46	9.78
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43
Lead Thickness	С	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width	В	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing	§ eB	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15
* Controlling Parameter							

Notes:

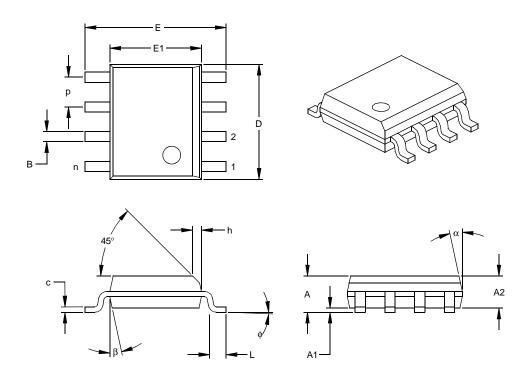
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.
JEDEC Equivalent: MS-001

Drawing No. C04-018

^{*} Controlling Parameter § Significant Characteristic

www.DataSheet4LL.com

8-Lead Plastic Small Outline (OA) - Narrow, 150 mil (SOIC)



	Units	INCHES*			MILLIMETERS		
Dimension	Limits	MIN	MOM	MAX	MIN	NOM	MAX
Number of Pins	n	·-	8			8	
Pitch	р		.050			1.27	
Overall Height	Α	.053	.061	.069	1.35	1.55	1.75
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25
Overall Width	Е	.228	.237	.244	5.79	6.02	6.20
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99
Overall Length	D	.189	.193	.197	4.80	4.90	5.00
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51
Foot Length	L	.019	.025	.030	0.48	0.62	0.76
Foot Angle	ф	0	4	8	0	4	8
Lead Thickness	С	.008	.009	.010	0.20	0.23	0.25
Lead Width	В	.013	.017	.020	0.33	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

^{*} Controlling Parameter

Notes

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed

.010" (0.254mm) per side.
JEDEC Equivalent: MS-012
Drawing No. C04-057

[§] Significant Characteristic

www.DataSheet4U.com

NOTES:

www.DataSheet4LL.com

APPENDIX A: REVISION HISTORY

Revision A (May 2005)

• Original Release of this Document.

www.DataSheet4U.com

NOTES:

www.DataSheet4LL.com

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. X	<u>xx </u>	Exa	amples:
	erature Package Tape & Reel	a)	TC4421AVAT: 9A High-Speed Inverting MOSFET Driver, TO-220 package, -40°C to +125°C.
Device:	TC4421A: 9A High-Speed MOSFET Driver, Inverting TC4422A: 9A High-Speed MOSFET Driver, Non-Inverting	b)	TC4421AVOA: 9A High-Speed Inverting MOSFET Driver, SOIC package, -40°C to +125°C.
Temperature Range: Package: *	V = -40°C to +125°C AT = TO-220, 5-lead	c)	TC4421AVMF: 9A High-Speed Inverting MOSFET Driver, DFN package,
	MF = Dual, Flat, No-Lead (6x5 mm Body), 8-lead MF713 = Dual, Flat, No-Lead (6x5 mm Body), 8-lead (Tape and Reel) PA = Plastic DIP (300 mil Body), 8-lead OA = Plastic SOIC (150 mil Body), 8-lead OA713 = Plastic SOIC (150 mil Body), 8-lead (Tape and Reel)	a)	-40°C to +125°C. TC4422AVPA: 9A High-Speed Non-Inverting MOSFET Driver, PDIP package, -40°C to +125°C.
	*All package offerings are Pb Free (Lead Free).	b)	TC4422AVOA: 9A High-Speed Non-Inverting MOSFET Driver, SOIC package, -40°C to +125°C.
		c)	TC4422AVMF: 9A High-Speed Non-Inverting MOSFET Driver, DFN package, -40°C to +125°C.

www.DataSheet4U.com

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not
 mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WAR-RANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, Accuron, dsPIC, KEELOQ, microID, MPLAB, PIC, PICmicro, PICSTART, PRO MATE, PowerSmart, rfPIC, and SmartShunt are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AmpLab, FilterLab, Migratable Memory, MXDEV, MXLAB, PICMASTER, SEEVAL, SmartSensor and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, dsPICDEM, dsPICDEM.net, dsPICworks, ECAN, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, Linear Active Thermistor, MPASM, MPLIB, MPLINK, MPSIM, PICkit, PICDEM, PICDEM.net, PICLAB, PICtail, PowerCal, PowerInfo, PowerMate, PowerTool, rfLAB, rfPICDEM, Select Mode, Smart Serial, SmartTel, Total Endurance and WiperLock are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2005, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

QUALITY MANAGEMENT SYSTEM
CERTIFIED BY DNV

ISO/TS 16949:2002

Microchip received ISO/TS-16949:2002 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona and Mountain View, California in October 2003. The Company's quality system processes and procedures are for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200

Tel: 480-792-7200 Fax: 480-792-7277 Technical Support:

http://support.microchip.com

Web Address: www.microchip.com

Atlanta

Alpharetta, GA Tel: 770-640-0034 Fax: 770-640-0307

Boston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

Kokomo, IN Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

San Jose

Mountain View, CA Tel: 650-215-1444 Fax: 650-961-0286

Toronto

Mississauga, Ontario,

Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Australia - Sydney

Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing

Tel: 86-10-8528-2100 Fax: 86-10-8528-2104

China - Chengdu

Tel: 86-28-8676-6200 Fax: 86-28-8676-6599

China - Fuzhou

Tel: 86-591-8750-3506 Fax: 86-591-8750-3521

China - Hong Kong SAR

Tel: 852-2401-1200 Fax: 852-2401-3431

China - Shanghai Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Shunde

Tel: 86-757-2839-5507 Fax: 86-757-2839-5571

China - Qingdao

Tel: 86-532-502-7355 Fax: 86-532-502-7205

ASIA/PACIFIC

India - Bangalore

Tel: 91-80-2229-0061 Fax: 91-80-2229-0062

India - New Delhi

Tel: 91-11-5160-8631 Fax: 91-11-5160-8632

Japan - Kanagawa

Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Penang

Tel:011-604-646-8870 Fax:011-604-646-5086

Philippines - Manila

Tel: 011-632-634-9065 Fax: 011-632-634-9069

Singapore

Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Kaohsiung Tel: 886-7-536-4818

Fax: 886-7-536-4803

Taiwan - Taipei

Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Taiwan - Hsinchu Tel: 886-3-572-9526 Fax: 886-3-572-6459

EUROPE

Austria - Weis

Tel: 43-7242-2244-399 Fax: 43-7242-2244-393

Denmark - Ballerup

Tel: 45-4450-2828 Fax: 45-4485-2829

France - Massy Tel: 33-1-69-53-63

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Ismaning

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen Tel: 31-416-690399

Fax: 31-416-690340 England - Berkshire

Tel: 44-118-921-5869 Fax: 44-118-921-5820

04/20/05